



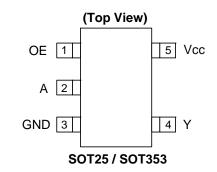
Description

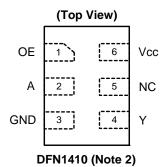
The 74LVCE1G126 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a LOW-level is applied to the output enable (OE) pin. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

Features

- Extended Supply Voltage Range from 1.4 to 5.5V
- Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
 Exceeds 200-V Machine Model (A115-A)
 Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- SOT25, SOT353 and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

Pin Assignments





Applications

- Voltage Level Shifting
- Bus Driver / Repeater
- Power Down Signal Isolation
- General Purpose Logic
 - Wide array of products such as.
 - o PCs, networking, notebooks, netbooks, PDAs
 - o Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Cell Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders
- Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.
 - 2. Pin 2 and pin 5 of the DFN1410 package are internally connected.

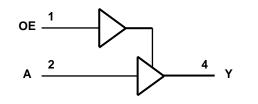


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Pin Descriptions

Pin Name	Description
OE	Output Enable (active high)
А	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage

Logic Diagram



Function Table

Inp	Output			
OE				
Н	Н	Н		
Н	L	L		
L	Х	Z		



Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
Ι _{ΟΚ}	Output Clamp Current	-50	mA
Ι _Ο	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Conditions (Note 4)

Symbol		Parameter	Min	Max	Unit	
		Operating	1.4	5.5	V	
V _{cc}	Operating Voltage	Data retention only	1.2		V	
		$V_{\rm CC} = 1.4 \text{ V}$ to 1.95 V	0.65 X V _{CC}			
N/		$V_{\rm CC}$ = 2.3 V to 2.7 V	1.7		V	
V _{IH}	High Level Input Voltage	$V_{CC} = 3 V$ to 3.6 V	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 X V _{CC}			
		$V_{\rm CC} = 1.4 \text{ V}$ to 1.95 V		0.35 X V_{CC}		
M	V _{IL} Low Level Input Voltage	$V_{\rm CC}$ = 2.3 V to 2.7 V		0.7	V	
V _{IL}	Low Level input voltage	$V_{CC} = 3 V$ to 3.6 V		0.8	v	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.3 X V _{CC}		
VI	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V _{cc}	V	
		Vcc=1.4 V		-3		
	High Level Output	V _{CC} = 1.65 V		-4		
		$V_{CC} = 2.3 V$		-8	mA	
I _{ОН}	Current	$V_{\rm CC} = 3 V$		-16		
				-24		
		$V_{CC} = 4.5 V$		-32		
		Vcc=1.4 V		3		
		V _{CC} = 1.65 V		4		
	Low Level Output	$V_{CC} = 2.3 V$		8	mA	
I _{OL}	Current			16		
		$V_{CC} = 3 V$		24		
		$V_{\rm CC} = 4.5 \text{ V}$		32		
		$V_{\rm CC} = 1.4$ to 3V		20		
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
$\Delta t/\Delta V$ rate	$V_{CC} = 5 V \pm 0.5 V$		5			
T _A	Operating free-air temperature		-40	85	٥C	

Note: 4. Unused inputs should be held at Vcc or Ground.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Electrical Characteristics (All typical values are at Vcc = 3.3V, T_A = 25° C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit	
		I _{OH} = -100μA	1.4 V to 5.5V	V _{CC} -0.1				
		I _{OH} = -3mA	1.4 V	1.05				
V _{он}	High Level Output Voltage	$I_{OH} = -4mA$	1.65 V	1.2				
		I _{OH} = -8mA	2.3V	1.9			V	
	Vollage	I _{OH} = -16mA	3 V	2.4				
		I _{OH} = -24mA	3 V	2.3				
		I _{OH} = -32mA	4.5 V	3.8				
		I _{OL} = 100μA	1.4 V to 5.5V			0.1		
		$I_{OL} = 3mA$	1.4V			.4		
		$I_{OL} = 4mA$	1.65 V			0.45		
V _{OL}	Low Level Output Voltage	$I_{OL} = 8mA$	2.3V			0.3	V	
	Vollage	I _{OL} = 16mA	3 V			0.4		
		$I_{OL} = 24 \text{mA}$	5 V			0.55		
		$I_{OL} = 32 \text{mA}$	4.5			0.55		
I _I	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μA	
I _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 5.5V$	0			± 10	μA	
I _{oz}	Z State Leakage Current	$V_0 = 0$ to 5.5V	3.6V			10	μA	
I _{CC}	Supply Current	$V_1 = 5.5V$ of GND $I_0=0$	1.4 V to 5.5V			10	μA	
ΔI_{CC}	Additional Supply Current	One input at V_{CC} – 0.6 V Other inputs at V_{CC} or GND	3 V to 5.5V			500	μA	
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		3.5		pF	
		SOT25	(Note 5)		204			
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5)		371		°C/W	
		DFN1410	(Note 5)		430			
		SOT25	(Note 5)		52			
θ_{JC}	Thermal Resistance Junction-to-Case	SOU353 (NOTA 5) 12		143		°C/W		
	Junction-to-Case	DFN1410	(Note 5)	1	190		1	

Over recommended free-air temperature range (unless otherwise noted)

Note: 5. Test condition for SOT25, SOT353 and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Switching Characteristics

Parameter	From	-						то	± 0.1V		Vcc = 1.8 V ± 0.15V		Vcc = 2.5 V ± 0.2V		Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V		Unit
			(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Мах	Min	Мах	•					
	t _{pd}	А	Y	1.7	6.9	1.1	4.8	0.4	3.6	0.4	3	0.4	3	ns					

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From (Input)				то	Vcc = ± 0			: 1.8 V .15V		: 2.5 V).2V		: 3.3 V).3V	: Vcc ± 0	= 5 V).5V	Unit
		(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	•			
t _{pd}	А	Y	2.6	8	1.8	5.6	0.8	4.4	0.8	3.6	0.9	3.6	ns			
t _{en}	OE	Y	2.8	9.4	1.9	6.5	1	5.2	0.9	4.3	0.9	4.3				
t _{dis}	OE	Y	1.6	9.8	1.1	6.8	0.8	4.4	0.8	4.5	0.9	3.7				

Operating Characteristics

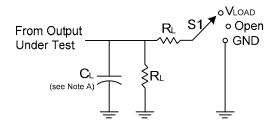
T_A = 25 °C

	Parame	ter	Test Conditions	Vcc = 1.5 V TYP	Vcc = 1.8 V TYP	Vcc = 2.5 V TYP	Vcc = 3.3 V TYP	Vcc = 5 V TYP	Unit
C _{pd}	Power dissipation	Outputs enabled	f = 10 MHz	19	19	19	19	19	pF
Upd	capacitance	Outputs disabled		2	2	2	3	4	μL



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

Vcc	In	puts	N	C	D.
VCC	VI	t _r /t _f	V _M	CL	RL
1.5V±0.1V	V _{cc}	≤2ns	V _{CC} /2	15pF	1MΩ
1.8V±0.15V	V _{cc}	≤2ns	V _{cc} /2	15pF	1MΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	15pF	1MΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1MΩ
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	15pF	1MΩ

Output

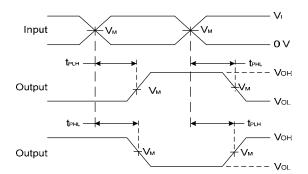
Control

Output

Waveform 1

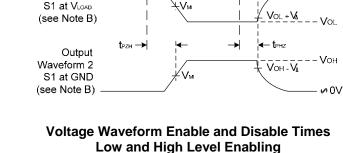


Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
 - E. t_{PZL} and t_{PZH} are the same as t_{EN} .
 - F. t_{PLH} and t_{PHL} are the same as t_{PD} .



V™

t_{PZL}

Figure 1. Load Circuit and Voltage Waveforms

Vi

0 V

VLOAD/2

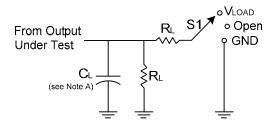
Vм

🔶 teuz



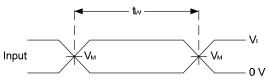
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information (Continued)

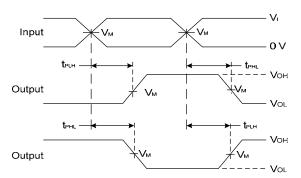


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

Vcc	Ing	outs	V _M	CL	RL
	Vi	t _r /t _f	• 141	Ϋ́́	
1.5V±0.1V	V _{cc}	≤2ns	V _{CC} /2	30pF	1KΩ
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1KΩ
2.5V±0.2V	V _{cc}	≤2ns	V _{CC} /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω



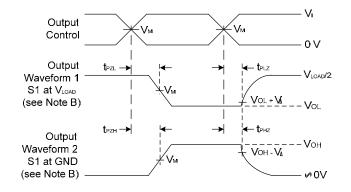
Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
 - E. t_{PZL} and t_{PZH} are the same as t_{EN0}
 - F. t_{PLH} and t_{PHL} are the same as $t_{\mathsf{PD.}}$

Figure 2. Load Circuit and Voltage Waveforms

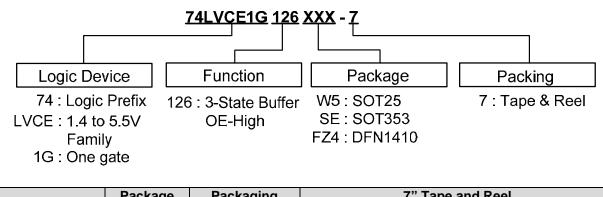


Voltage Waveform Enable and Disable Times Low and High Level Enabling



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Ordering Information



	Device	Package Code	Packaging (Note 5)	7" Tape and Reel		
	Device			Quantity	Part Number Suffix	
Pb ,	74LVCE1G126W5-7	W6	SOT25	3000/Tape & Reel	-7	
Pb ,	74LVCE1G126SE-7	SE	SOT353	3000/Tape & Reel	-7	
Pb ,	74LVCE1G126FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7	

Note: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

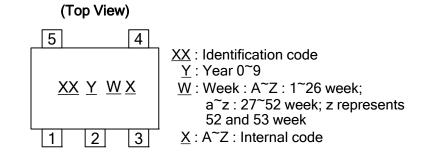
74LVCE1G126 Document number: DS32217 Rev. 3 - 2



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Marking Information

(1) SOT25 and SOT353



	Part Number	Package	Identification Code
Γ	74LVCE1G126W5	SOT25	PZ
	74LVCE1G126SE	SOT353	PZ

(2) DFN1410

(Top View)



- XX: Identification Code
- <u>Y</u> : Year : 0~9
- <u>W</u>: Week : A~Z : 1~26 week; a~z : 27~52 week; z represents 52 and 53 week
- \underline{X} : A~Z : Internal code

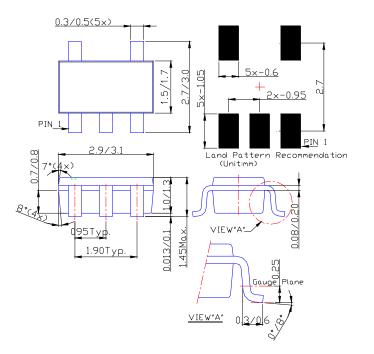
Part Number	Package	Identification Code
74LVCE1G126FZ4	DFN1410	PZ



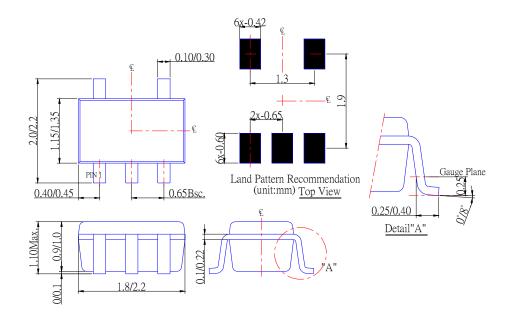
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



(2) Package Type: SOT353



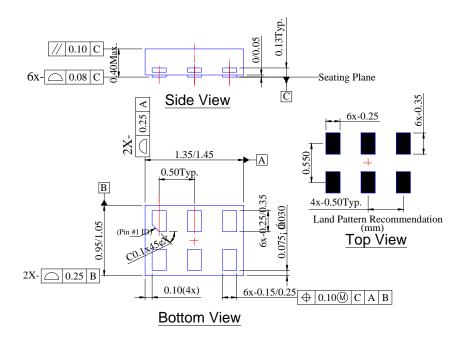
74LVCE1G126 Document number: DS32217 Rev. 3 - 2



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Package Outline Dimensions (All Dimensions in mm)

(3) Package Type: DFN1410

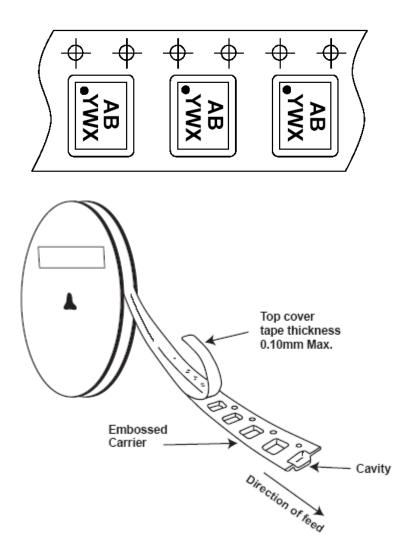




SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Taping Orientation (Note 7)

For DFN1410







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